

Form PTO 1449 Rev. 7-80 U.S. Department of Commerce Patent and Trademark Office LIST OF PRIOR ART CITED BY APPLICANT (Use Several Sheets If Necessary)	Atty. Docket No. CH8498US	Serial No. To Be Assigned
Applicant Jagdish Narayan et al		
Filing Date Herewith		Group No.

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EXAMINER INITIAL	AA	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	3,808,109	04/30/74	Schauer	204	38 A	
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	AC	4,036,708	07/19/77	Feit et al	204	38	
	AD	5,281,485	01/25/94	Colgan et al	428	457	
	AE	5,406,123	04/11/95	Narayan	257	767	
	AF	5,882,399	03/16/99	Ngan et al	117	89	
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	AH	6,291,885 B1	09/18/01	Cabral, Jr. et al	257	751	
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	AK	6,458,255 B2	10/01/02	Chiang et al	204	192.5	

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